Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

A systematic investigation of chromium and vanadium impurities in Janus Ga_2SO monolayer towards spintronic applications

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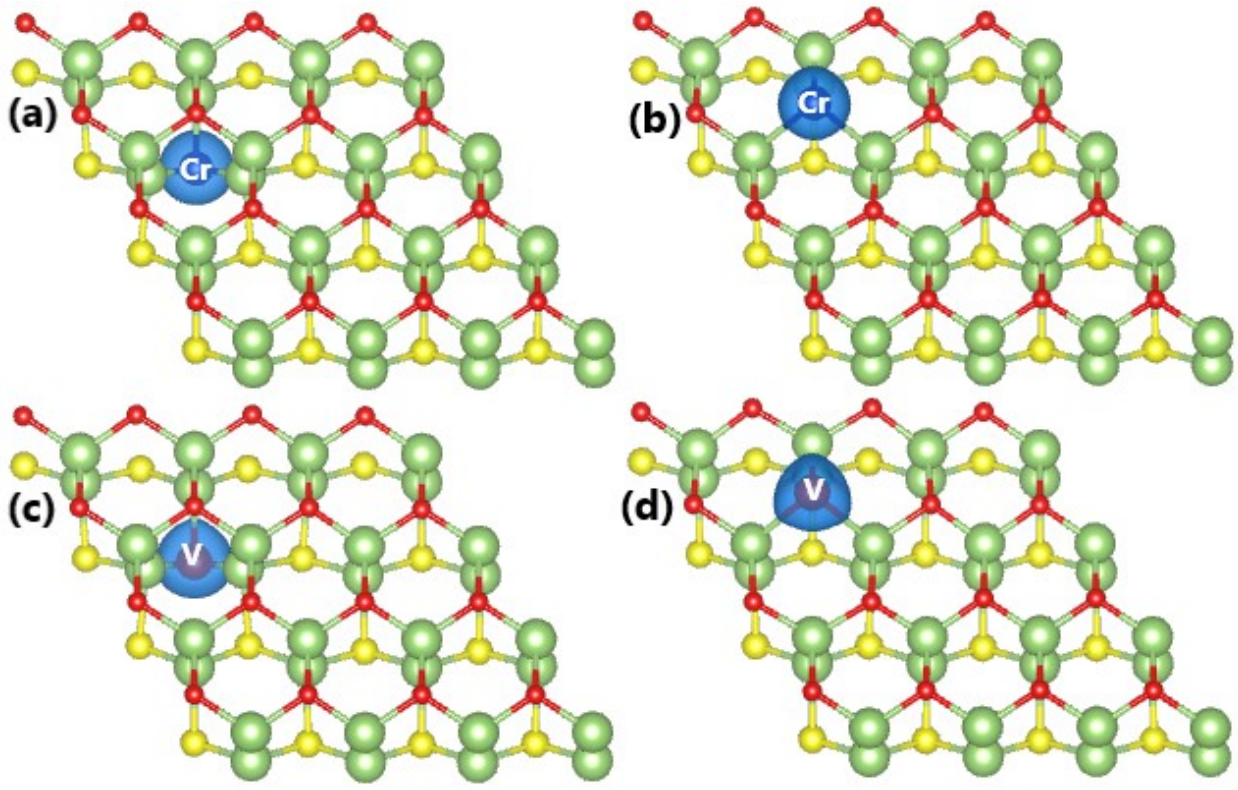

Figure S1: Spin density (Iso-surface value: 0.02 e/Å^3) in (a) Cr_S, (b) Cr_O, (c) V_S, and (d) V_O system.

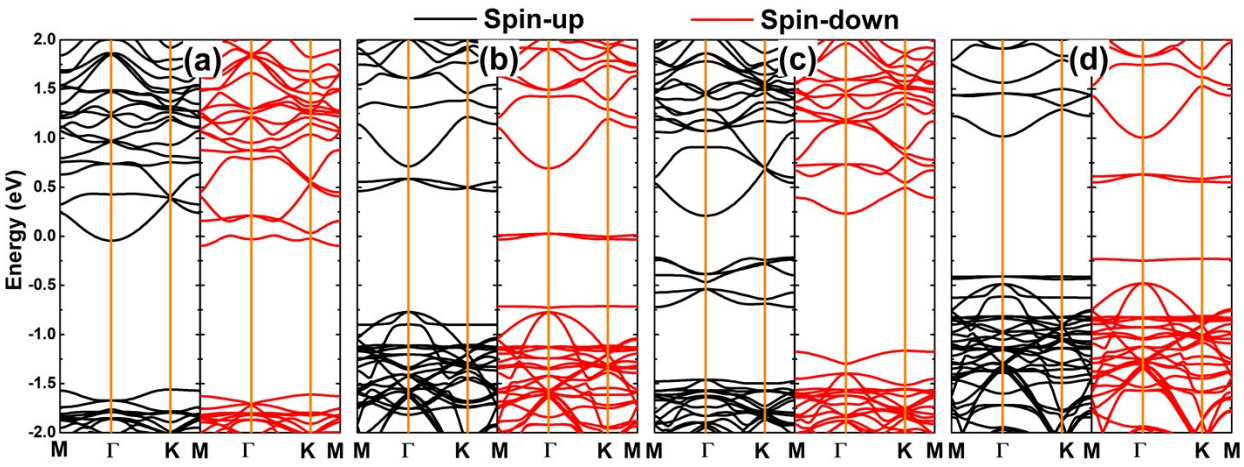

Figure S2: Spin-polarized band structure (The Fermi level is set to 0 eV) of (a) Cr_S, (b) Cr_O, (c) V_S, and (d) V_O system.

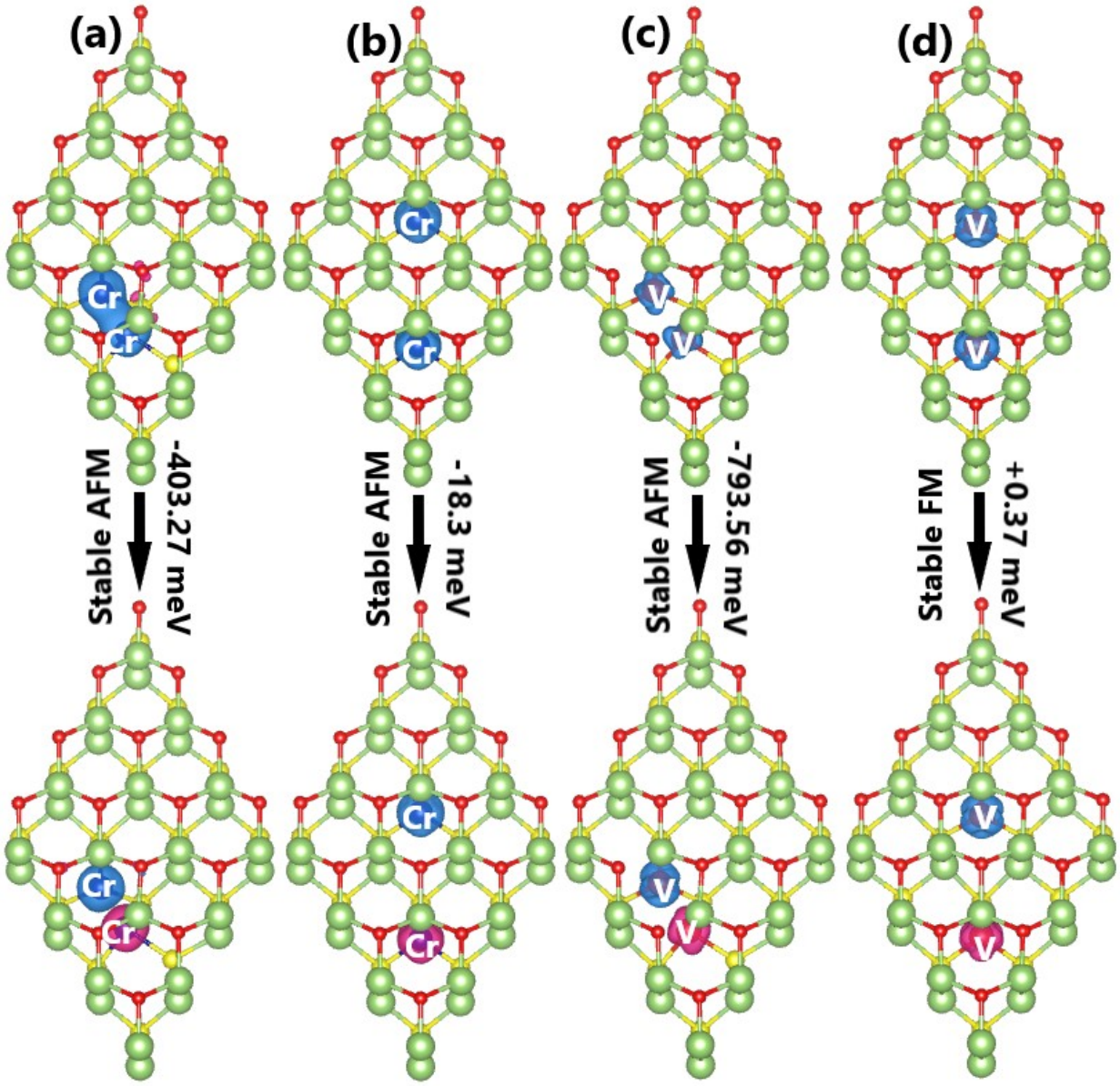

Figure S3: Energy of magnetic state transition in Ga_2SO monolayer doped with (a-b) Cr atoms and (c-d) V atoms at Ga1 sublattice.

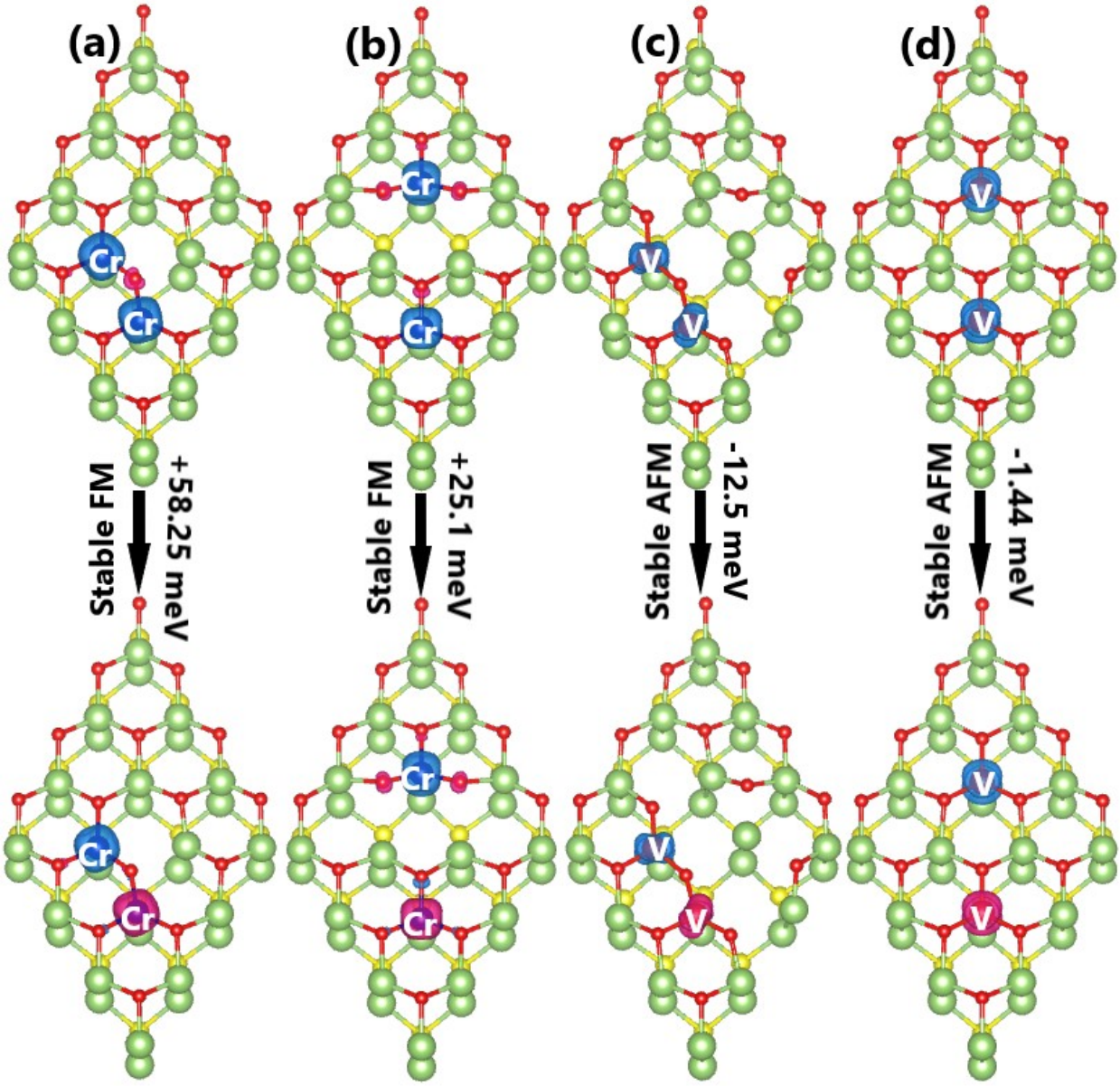

Figure S4: Energy of magnetic state transition in Ga_2SO monolayer doped with (a-b) Cr atoms and (c-d) V atoms at Ga2 sublattice.